TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT process)

# 2SC3074

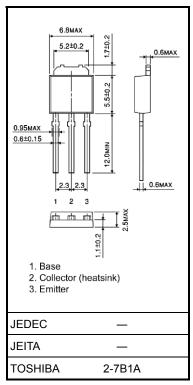
### **High Current Switching Applications**

- Low collector saturation voltage: VCE (sat) = 0.4 V (max) (IC = 3 A)
- High speed switching time:  $t_{stg} = 1.0 \mu s$  (typ)
- Complementary to 2SA1244

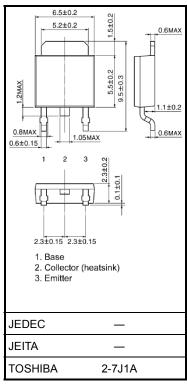
### **Maximum Ratings (Ta = 25°C)**

Characteristics		Symbol	Rating	Unit	
Collector-base voltage		V <sub>CBO</sub>	60	V	
Collector-emitter voltage		V <sub>CEO</sub>	50	V	
Emitter-base voltage		V <sub>EBO</sub>	5	V	
Collector current		Ic	5	Α	
Base current		Ι <sub>Β</sub>	1	Α	
Collector power dissipation	Ta = 25°C	P <sub>C</sub>	1.0	W	
	Tc = 25°C		20		
Junction temperature		Тј	150	°C	
Storage temperature range		T <sub>stg</sub>	-55 to 150	°C	

Unit: mm



Weight: 0.36 g (typ.)



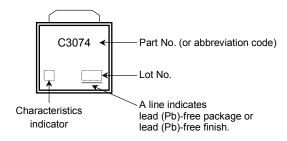
Weight: 0.36 g (typ.)

## Electrical Characteristics (Ta = 25°C)

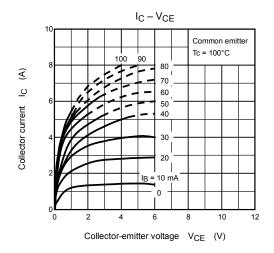
Chara	acteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off of	current	I <sub>CBO</sub>	V <sub>CB</sub> = 50 V, I <sub>E</sub> = 0	_	_	1	μA
Emitter cut-off cu	rrent	I <sub>EBO</sub>	V <sub>EB</sub> = 5 V, I <sub>C</sub> = 0	-	_	1	μA
Collector-emitter	breakdown voltage	V (BR) CEO	I <sub>C</sub> = 10 mA, I <sub>B</sub> = 0	50	_	_	V
DC current gain		h <sub>FE (1)</sub> (Note)	V <sub>CE</sub> = 1 V, I <sub>C</sub> = 1 A	70	_	240	
		h <sub>FE (2)</sub>	V <sub>CE</sub> = 1 V, I <sub>C</sub> = 3 A	30	_	_	
Collector-emitter	saturation voltage	V <sub>CE (sat)</sub>	I <sub>C</sub> = 3 A, I <sub>B</sub> = 0.15 A	_	0.2	0.4	V
Base-emitter satu	ıration voltage	V <sub>BE (sat)</sub>	I <sub>C</sub> = 3 A, I <sub>B</sub> = 0.15 A	_	0.9	1.2	V
Transition freque	ncy	f <sub>T</sub>	V <sub>CE</sub> = 4 V, I <sub>C</sub> = 1 A		120	_	MHz
Collector output capacitance		C <sub>ob</sub>	V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0, f = 1 MHz		80	_	pF
Switching time S	Turn-on time	t <sub>on</sub>	20 $\mu$ s $B_1$ OUTPUT $B_2$ $B_2$ $C_{CC} = 30 \text{ V}$ $ B_1 = -I_{B2} = 0.15 \text{ A},$ Duty cycle $\leq 1\%$	_	0.1	_	
	Storage time	t <sub>stg</sub>		l	1.0		μs
	Fall time	t <sub>f</sub>		_	0.1	_	

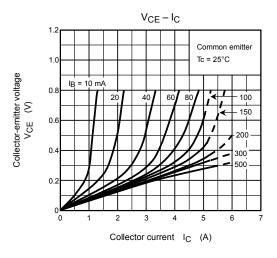
Note:  $h_{FE(1)}$  classification O: 70 to 140, Y: 120 to 240

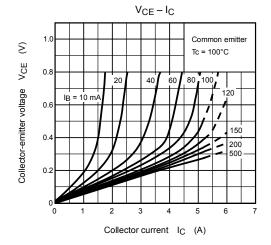
### Marking

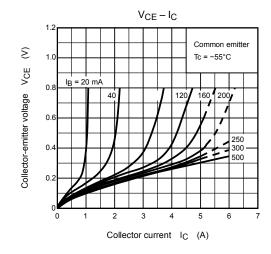


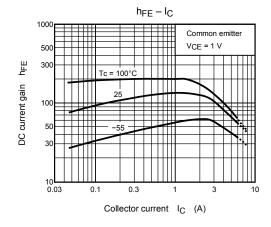
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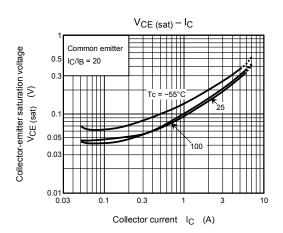


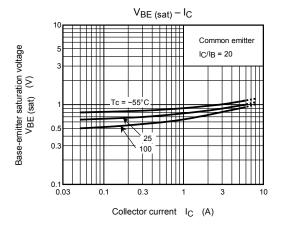


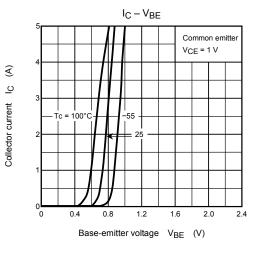


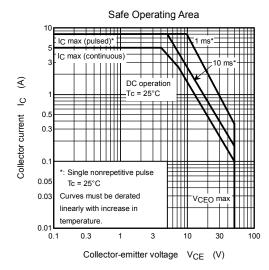


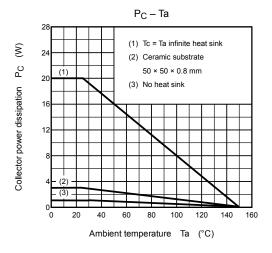












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